L .	Hits	Search Text	DB	Time stamp
Number	97	((first or second) near (tft or (thin near film	USPAT;	2004/07/25
202	31	near transistor))) and ((first or second) near	US-PGPUB;	20:23
		(gate near (oxide or insulator or dielectric	EPO; JPO;	20:23
		or insulation)))	DERWENT;	
		or insulation)))	IBM_TDB	
	45	((first or second) near (tft or (thin near film	USPAT;	2004/07/25
	40	near transistor))) and ((first or second) near	US-PGPUB;	20:24
		(gate near (oxide or insulator or dielectric	EPO; JPO;	20:24
		,	, ,	
		or insulation))) and ((first or second) near	DERWENT;	
	32	(gate adj electrode))	IBM_TDB	2004/07/25
203	32	((first or second) near (tft or (thin near film	USPAT;	2004/07/25
		near transistor))) and ((first or second) near	US-PGPUB;	20:36
		(gate near (oxide or insulator or dielectric	EPO; JPO;	
		or insulation))) and ((first or second) near	DERWENT;	
		(gate adj electrode)) and ((low or high or	IBM_TDB	
		lightly or highly) near3 (dope or doped or		
		doping or impurity or density) or (Idd or hdd))		
204	3	((first or second) near (tft or (thin near film	USPAT;	2004/07/25
		near transistor))) and ((first or second) near	US-PGPUB;	20:30
		(gate near (oxide or insulator or dielectric	EPO; JPO;	
		or insulation))) and ((first or second) near	DERWENT;	
		(gate adj electrode)) and ((low or high or	IBM_TDB	
		lightly or highly) near3 (dope or doped or		
		doping or impurity or density) or (ldd or		
		hdd)) and (matsumoto or lee or wakai or		
		seo or yamaguchi)		
205	13	((first or second) near (tft or (thin near film	USPAT;	2004/07/25
		near transistor))) and ((first or second) near	US-PGPUB;	20:47
		(gate near (oxide or insulator or dielectric	EPO; JPO;	
		or insulation))) and ((first or second) near	DERWENT;	
		(gate adj electrode)) and ((low or high or	IBM_TDB	
		lightly or highly) near3 (dope or doped or	_	
		doping or impurity or density) or (Idd or		
		hdd)) and (semiconductor adj layer)		
206	6	((first or second) near (tft or (thin near film	USPAT;	2004/07/25
		near transistor))) and ((first or second) near	US-PGPUB;	20:40
		(gate near (oxide or insulator or dielectric	EPO; JPO;	
		or insulation))) and ((first or second) near	DERWENT;	
		(gate adj electrode)) and ((semiconductor	IBM_TDB	
		near layer) near10 ((low or high or lightly or		
		highly) near3 (dope or doped or doping or		
		impurity or density) or (ldd or hdd))) and		
		(semiconductor adj layer)		